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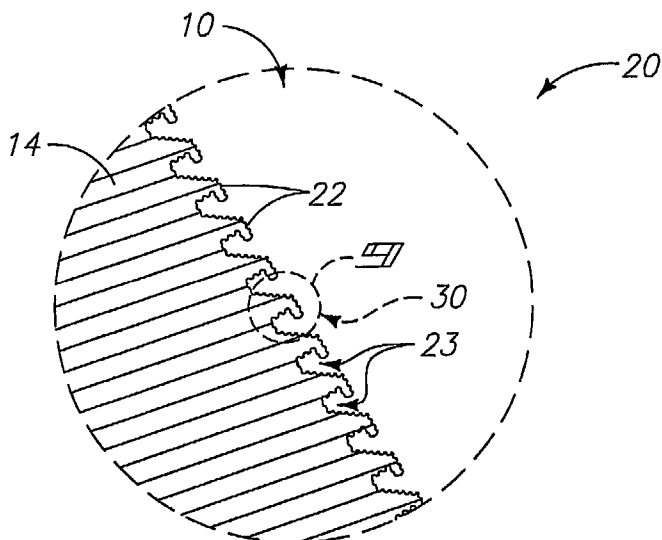
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(54) Title: PVD TARGET AND METHOD OF TREATING TARGET



(57) Abstract: The invention includes PVD targets having non-sputtered regions (such as, for example, sidewalls (14)), and particle-trapping features formed along the non-sputtered regions. In particular aspects, the particle-trapping features can comprise a pattern of bent projections (22) forming receptacles, and can comprise microstructures on the bent projections. The targets can be part of target/backing plate constructions (10), or can be monolithic. The invention also includes methods of forming particle-trapping features along sidewalls of a sputtering target or along sidewalls of a target/backing plate construction. The features can be formed by initially forming a pattern of projections along a sidewall. The projections can be bent and subsequently exposed to particles to form microstructures on the bent projections. The target has expanded regions (20 and 30) and cavities (23).

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